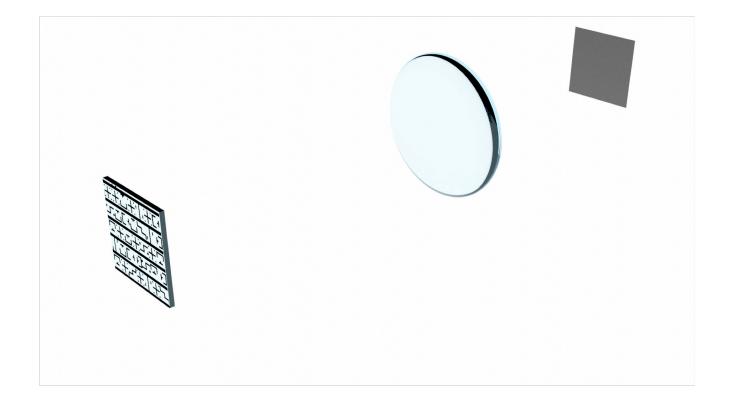
PAUL SCHERRER INSTITUT



EUV metrology with a compact accelerator-based source

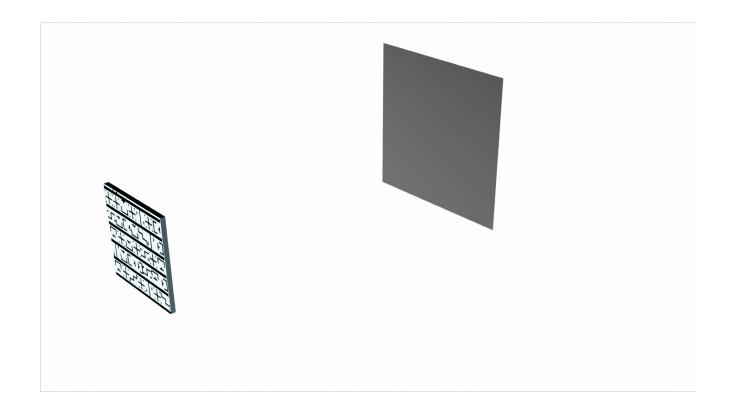
Yasin Ekinci Paul Scherrer Institut



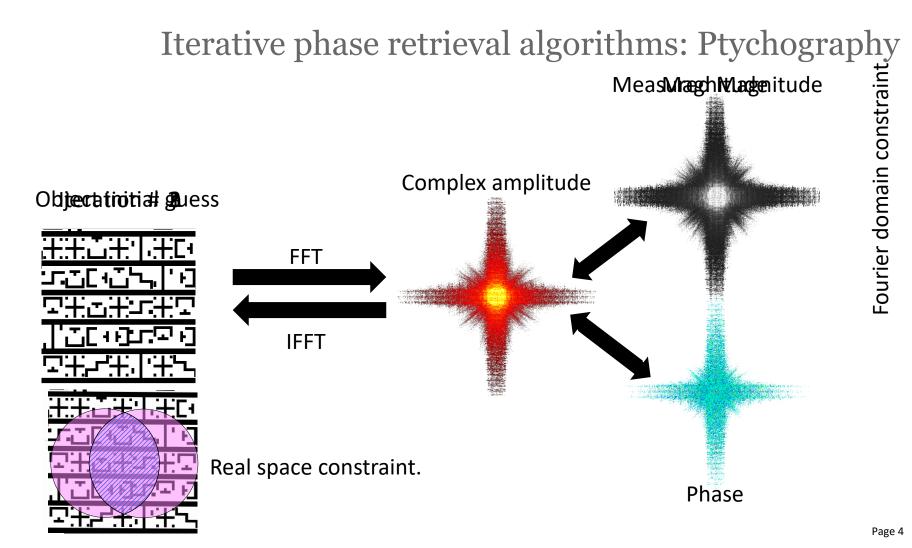




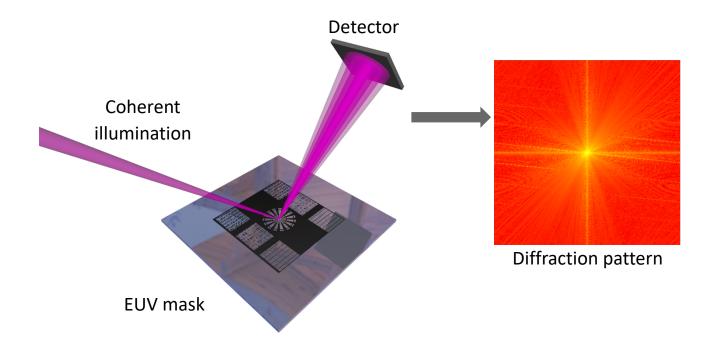
Lensless imaging (Coherent diffraction imaging)









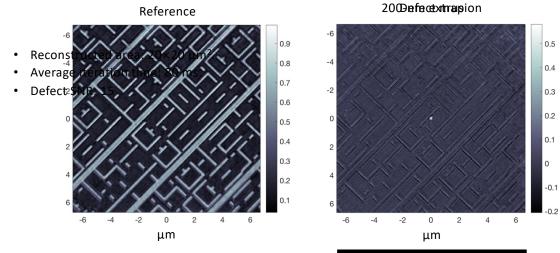


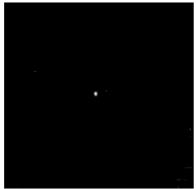
Actinic = EUV (13.5 nm), reflective, incidence angle = 6° Resolution = 35 nm



Pattern comparison for accurate defect localization

Die to die defect inspection: comparing a defect free area of the sample to a defective one.







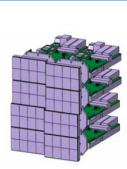
Roadmap for RESCAN

Target:

- S/N > 8.5 for all printable defects (~10 nm)
- scan time < 7 hours for 10x10 cm² mask



<u>RESCAN: Lensless Microscope</u> Continuous scanning 20 µm steps @ 2kHz = 3.5 hours)



<u>Jungfrau: High Performance Detector</u> 2 kHz frame rate High dynamic range: 10⁵



<u>Cosami: Mini synchrotron for EUV</u> Hight brightness Small footprint: 5x12 m²

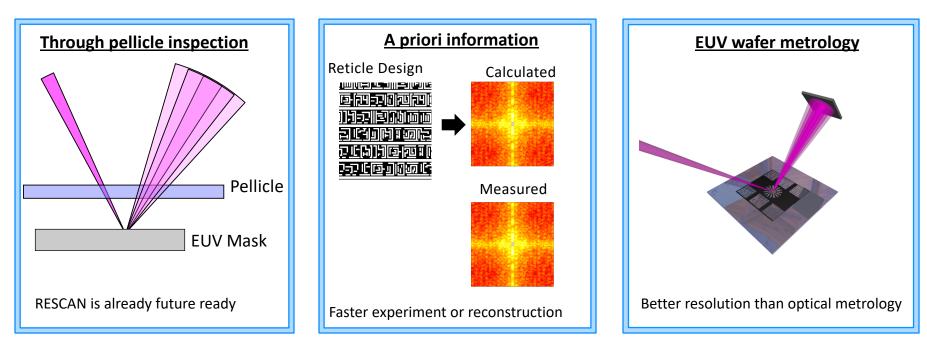
• RESCAN is a viable approach for a commercial mask inspection tool



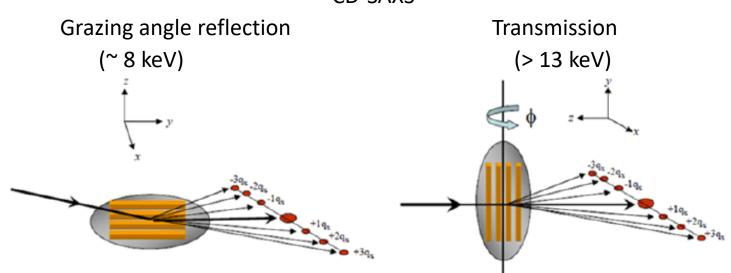
Using the advantages of lensless methods

Lensless imaging is flexible:

- Flexibility with the geometry and angles and wavelengths
- Flexibility: Change in algorithm instead of hardware for customized solution to a problem







Large spot on the wafer Lack of bright source Wafer thinning Lack of bright source

EUV Metrology sources

- EUV metrology sources for
 - -Actinic blank inspection (ABI)
 - -Actinic patterned mask inspection (APMI)
 - -Actinic mask review
 - -Actinic pellicle inspection
 - –Wafer metrology
 - Wafer inspection
 - Mask substrate inspection
- Requirements:
 - -High brightness
 - -High stability (intensity and beam position)
 - Compact (As compact as possible, But without increasing the machine complexity)
 - -Reliability: minimal down time, use proven technology, robust design
 - Minimize R&D costs, risks and lead time: Choose only proven concepts and technologies



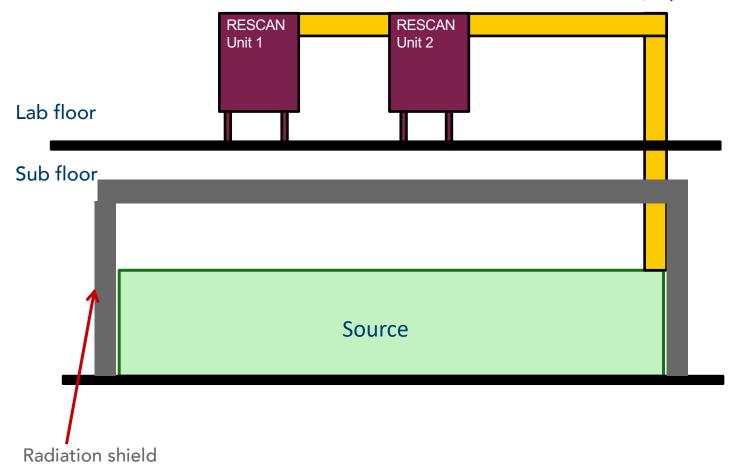
COSAMI: Compact Source for Actinic Mask Inspection

	Wavelength Flux Brilliance	13.5 nm ~100 mW ~ 10 ⁹ W/(mm ² ·strd)
	Beam energy/beam current	430 MeV/150 mA
	Pulse structure	~50 ps every 2 ns
	Injection system	Top-up mode
	Beam stability	0.1%
	Availability	>95%
	Reliability	<1% down time
Innovative solutions:	Footprint	5m × 12m

- \rightarrow adopt technology of Diffraction Limited Storage Rings
- \rightarrow Co-centric design: vertical stacking of booster and ring \rightarrow small footprint
- \rightarrow multi-bend magnet lattice
- ightarrow implementation of undulator
- \rightarrow combined function magnets
- ightarrow small vacuum chambers with NEG coating
- →Photo injector

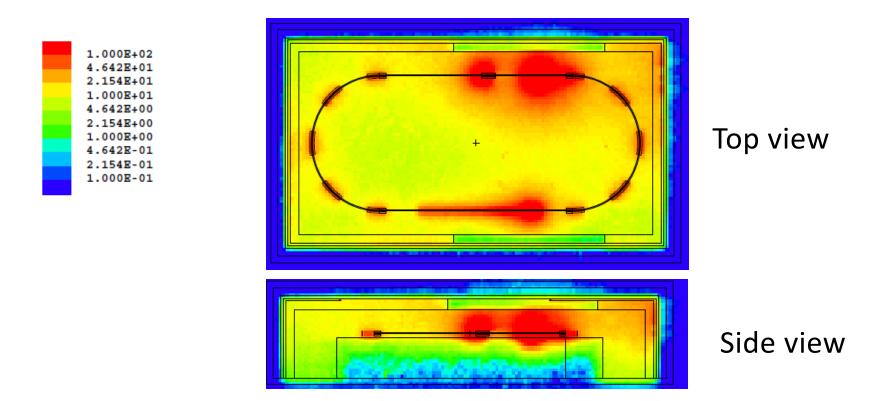


Beam delivery optics





Performed using codes MCNPX 2.7.0 (local) / MCNP 6.1 (outer wall) Loss rates ~ 1.2×10^8 electrons/s at 430 MeV \rightarrow ICRP data used to convert flux to dose rates. Losses dominated by storage ring.



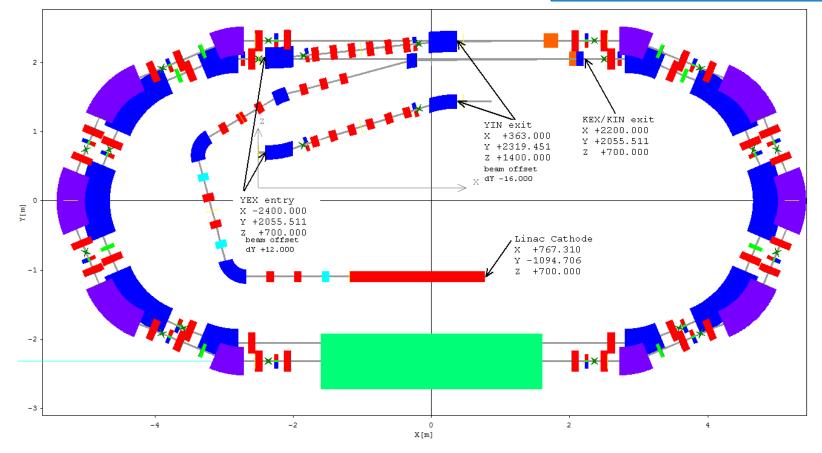
Blocks of concrete and polyethelyne required for adequate shielding. Optimization and local shielding will reduce the thickness. The requirements of regulatory agencies can be easily met.



Optics design

Race-track geometry: Two 5-bend achromat arcs and two straights. One straight for the undulator and one for injection and RF.

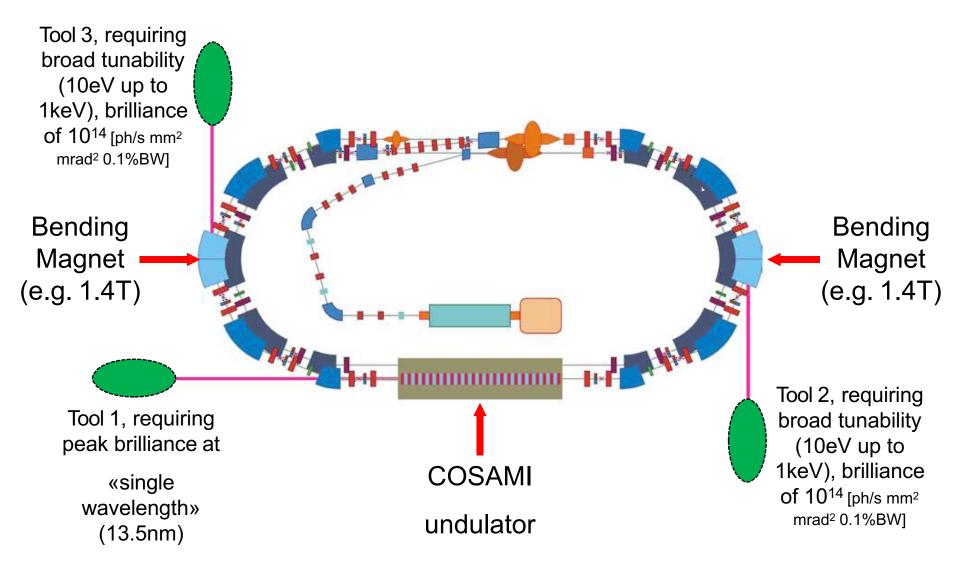
- Ring: 430 MeV, 25.8 m
- Booster: $43 \rightarrow 430$ MeV, 24.0 m
- BR transfer line -18.6° inclination
- LB transfer line
- Gun/Linac: 43 MeV, 2.1 m



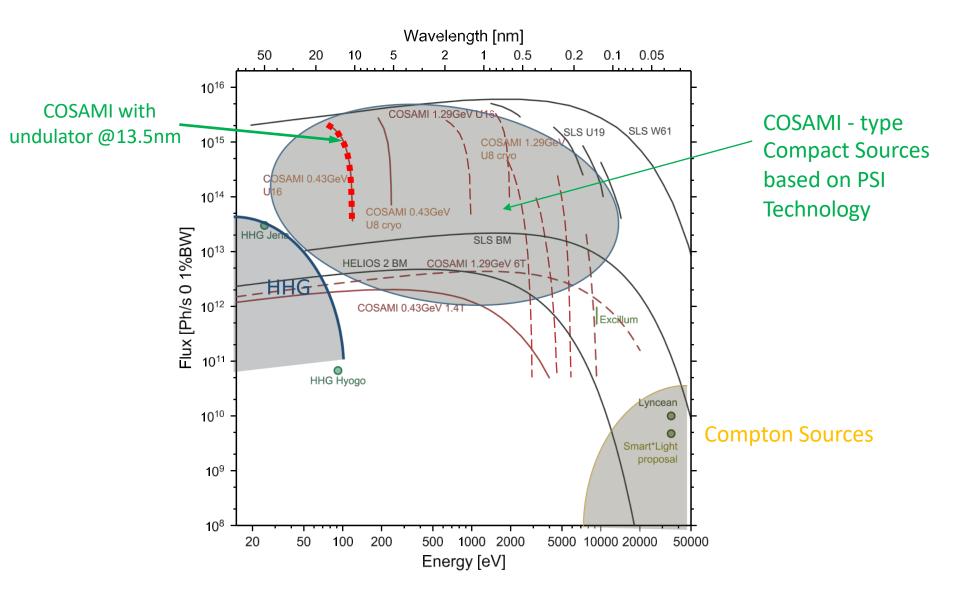
Lattice design is an iterative process to minimize the electron position, dispersion, and spread



COSAMI for broadband



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o EUV metrology has many advantages:

- Actnitic
- Short wavelength
- High material contrast
- Easier source
- Stay in reflection
- Penetration depth: 10-100 nm

o COSAMI design philosophy:

- Go for proven concepts and well established technologies
- Minimum delivery time by avoiding R&D and prototyping
- Compact design without compromising performance
- High-reliability as a production tool
- Ensuring radiation safety standards in production environment

COSAMI Design specifications

- Clean EUV power: >100 mW
- Tunable EUV wavelength
- High brightness: > 1GW/mm².std
- High intensity stability: 0.1%
- High reliability: up time > 99%
- Minimum maintenance: <5%



PSI: M. Aiba. R.M. Bergmann, T. Bieri, P. Craievich, M. Ehrlichman, C. Gough,P. Lerch, A. Mueller, M. Negrazus, C. Rosenberg, L. Schulz, L. Stingelin,V. Vrankovic, A. Zandonella Gallagher, R. Zennaro.

Advanced Accelerator Technologies



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Thank you for your attention.